TECHNICAL DATA SHEET

INFINEON TECHNOLOGIES

FZ1200R16KF4

IGBT module



General	
Semiconductor structure	**transistor/transistor**
Topology	**IGBT half-bridge**

Mechanical	
Case	**A-IHM130-2**
Electrical mounting	**screw**
Mechanical mounting	**screw**

Electrical Ratings	
DC-collector current (IC)	**1200 A**
Repetitive peak collector current (ICRM)	**2400 A**
Gate-emitter peak voltage (VGE)	**± 20 V**
Diode DC forward current (IF)	**1200 A**
Diode repetitive peak forw. current (IFRM)	**2400 A**

Thermal	
Junction temperature (tvj max)	**150 °C**

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